

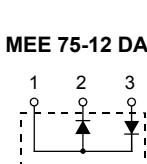
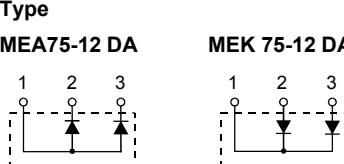
Fast Recovery Epitaxial Diode (FRED) Module

MEA 75-12 DA
MEK 75-12 DA
MEE 75-12 DA

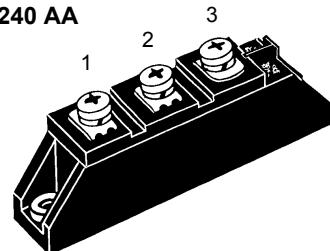
V_{RRM} = 1200 V
I_{FAV} = 75 A
t_{rr} = 250 ns

Preliminary data

V _{RSM} V	V _{RRM} V	Type	MEA75-12 DA	MEK 75-12 DA	MEE 75-12 DA
1200	1200		1 2 3	1 2 3	1 2 3



TO-240 AA



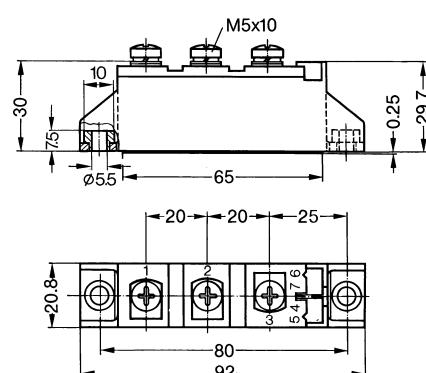
Symbol	Test Conditions	Maximum Ratings		
I _{FRMS}	T _{case} = 75 °C	107	A	
I _{FAV}	T _{case} = 75 °C; rectangular, d = 0.5	75	A	
I _{FRM}	t _p < 10 µs; rep. rating, pulse width limited by T _{VJM}	TBD	A	
I _{FSM}	T _{VJ} = 45°C; t = 10 ms (50 Hz), sine	1200	A	
	t = 8.3 ms (60 Hz), sine	1300	A	
	T _{VJ} = 150°C; t = 10 ms (50 Hz), sine	1080	A	
	t = 8.3 ms (60 Hz), sine	1170	A	
I ² t	T _{VJ} = 45°C; t = 10 ms (50 Hz), sine	7200	A ² s	
	t = 8.3 ms (60 Hz), sine	7100	A ² s	
	T _{VJ} = 150°C; t = 10 ms (50 Hz), sine	5800	A ² s	
	t = 8.3 ms (60 Hz), sine	5700	A ² s	
T _{VJ}		-40...+150	°C	
T _{stg}		-40...+125	°C	
T _{Hmax}		110	°C	
P _{tot}	T _{case} = 25°C	280	W	
V _{ISOL}	50/60 Hz, RMS t = 1 min	3000	V~	
	I _{ISOL} ≤ 1 mA t = 1 s	3600	V~	
M _d	Mounting torque (M5)	2.50-4/22-35	Nm/lb.in.	
	Terminal connection torque (M5)	2.50-4/22-35	Nm/lb.in.	
d _S	Creep distance on surface	12.7	mm	
d _A	Strike distance through air	9.6	mm	
a	Maximum allowable acceleration	50	m/s ²	
Weight		90	g	

Symbol	Test Conditions	Characteristic Values (per diode)	
		typ.	max.
I _R	T _{VJ} = 25°C V _R = V _{RRM}	2	mA
	T _{VJ} = 25°C V _R = 0.8 • V _{RRM}	0.5	mA
	T _{VJ} = 125°C V _R = 0.8 • V _{RRM}	34	mA
V _F	I _F = 100 A; T _{VJ} = 125°C	1.85	V
	T _{VJ} = 25°C	2.17	V
	I _F = 300 A; T _{VJ} = 125°C	2.58	V
	T _{VJ} = 25°C	2.64	V
V _{T0}	For power-loss calculations only	1.48	V
r _T		3.65	mΩ
R _{thJH}	DC current	0.550	K/W
R _{thJC}	DC current	0.450	K/W
t _{rr}	I _F = 150 A T _{VJ} = 100°C	250	ns
I _{RM}	V _R = 600 V T _{VJ} = 25°C	300	ns
	-di/dt = 200 A/µs T _{VJ} = 100°C	22	A
		33	A

Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions

Dimensions in mm (1 mm = 0.0394")



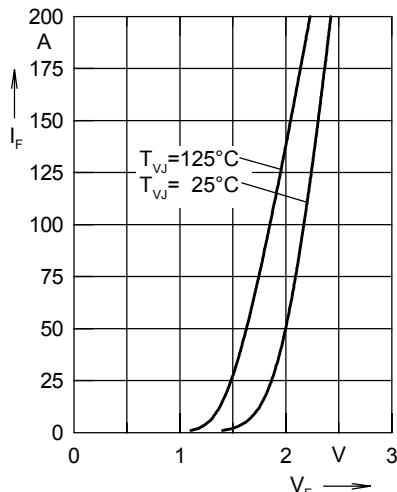


Fig. 1 Forward current I_F versus voltage drop V_F per leg

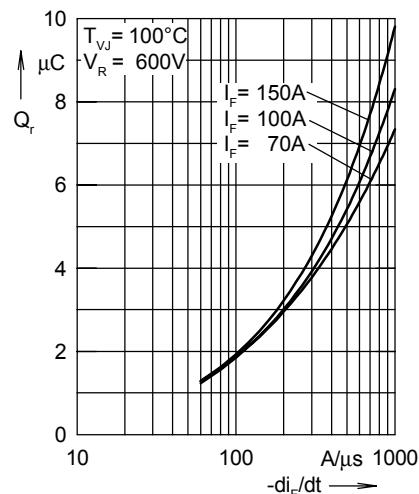


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

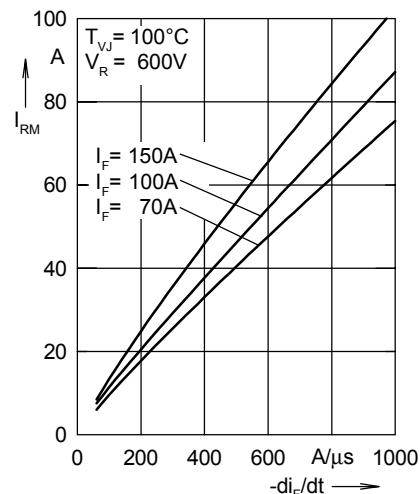


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

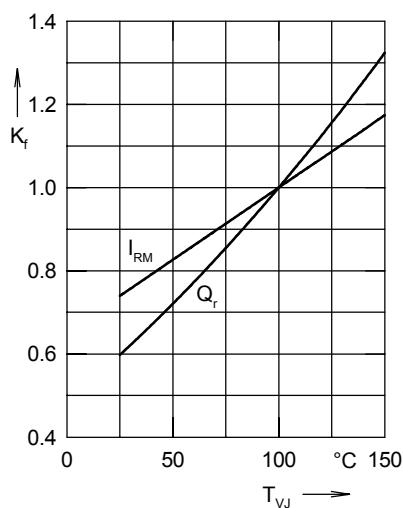


Fig. 4 Dynamic parameters Q_r , I_{RM} versus junction temperature T_{VJ}

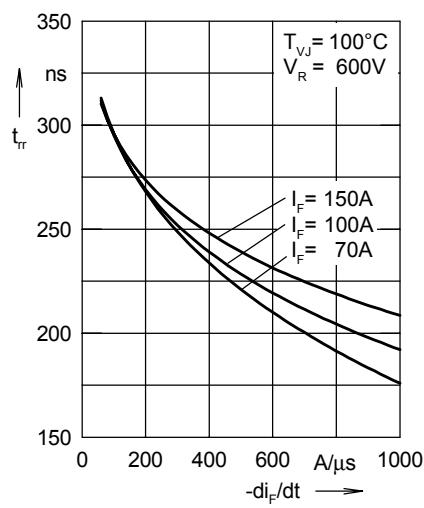


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

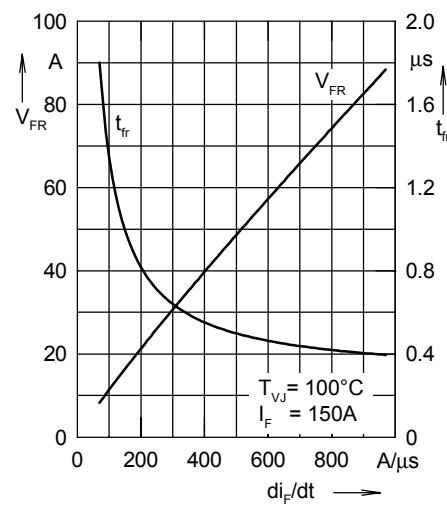


Fig. 6 Peak forward voltage V_{FR} and t_{rr} versus di_F/dt

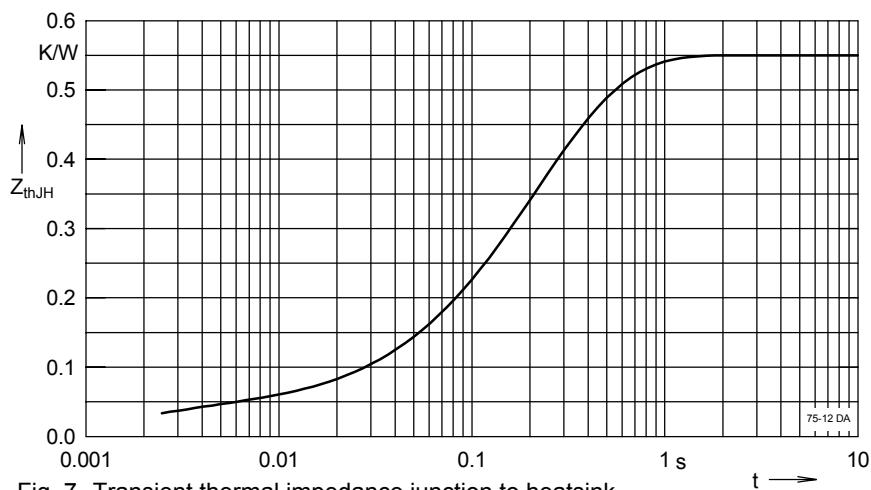


Fig. 7 Transient thermal impedance junction to heatsink

Constants for Z_{thJH} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.037	0.002
2	0.138	0.134
3	0.093	0.25
4	0.282	0.274

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